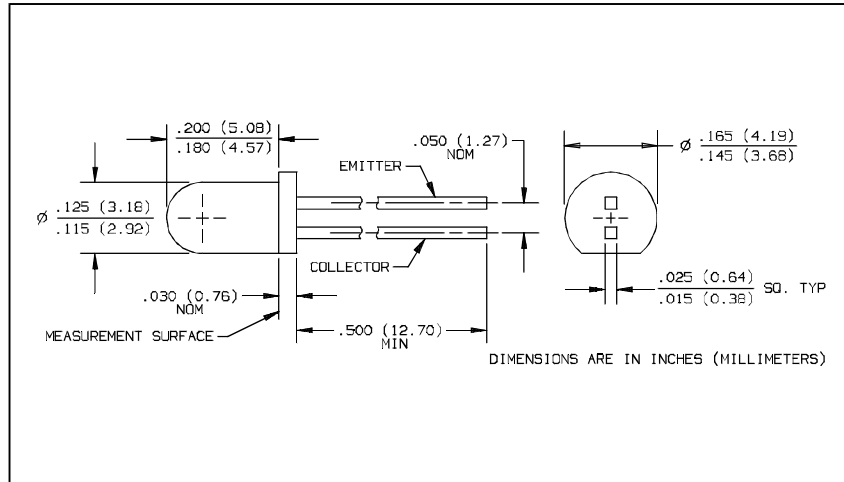


NPN Phototransistor with Base-Emitter Resistor Types OP705A, OP705B, OP705C, OP705D



Features

- Narrow receiving angle
- Variety of sensitivity ranges
- T-1 package style
- Small package size for space limited applications
- Base-emitter resistor provides ambient light protection

Description

The OP705 series devices consist of NPN silicon phototransistors molded in blue tinted epoxy packages. The narrow receiving angle provides excellent on-axis coupling. These devices are 100% production tested using infrared light for close correlation with Optek's GaAs and GaAlAs emitters.

The phototransistor has an internal base-emitter resistor which provides protection from low level ambient lighting conditions. This feature is also useful when the media being detected is semi-transparent to infrared light in interruptive applications.

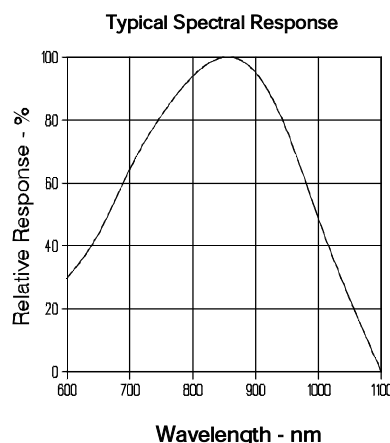
Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter Reverse Current	10 mA
Collector DC Current	30 mA
Storage and Operating Temperature Range	-40°C to $+100^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	100 mW ⁽²⁾

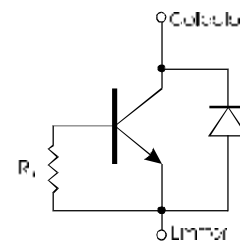
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. Max. 20 grams force may be applied to leads when soldering.
- (2) Derate linearly 1.33 mW/ $^\circ\text{C}$ above 25°C .
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) The knee point irradiance is defined as the irradiance required to increase $I_{C(ON)}$ to $50 \times A$.

Typical Performance Curves



Schematic

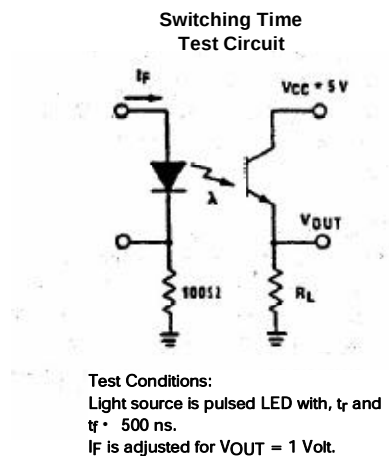
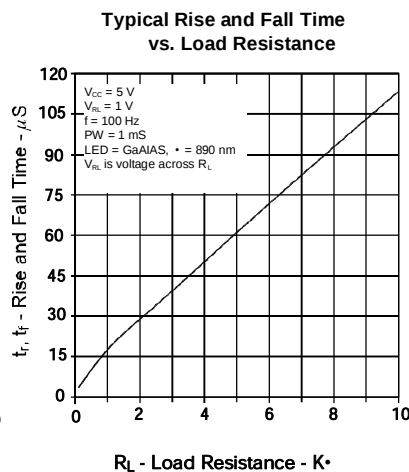
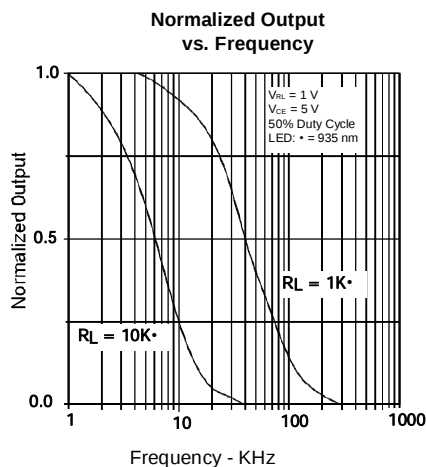
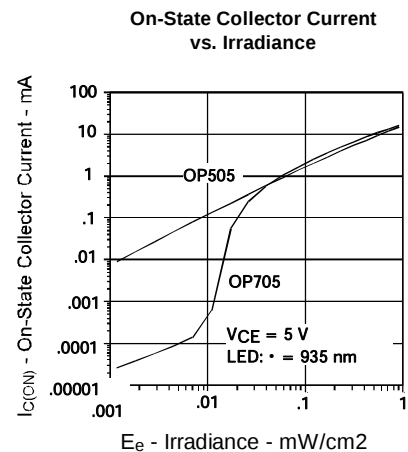
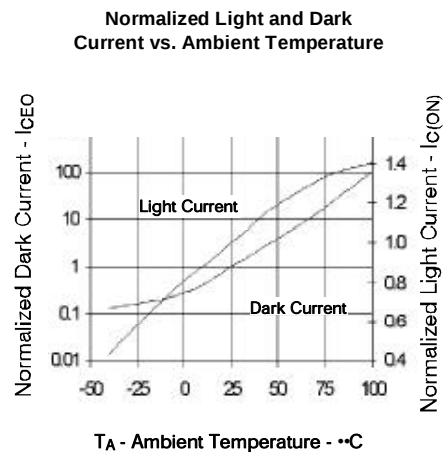
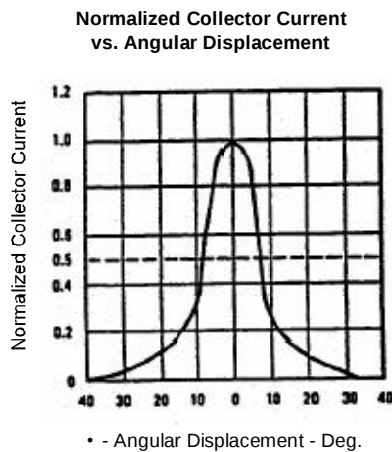


Types OP705A, OP705B, OP705C, OP705D

Electrical Characteristics ($T_A = 25^\circ \text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$I_{C(ON)}$	On-State Collector Current	OP705A OP705B OP705C OP705D	3.95 2.65 1.50 1.50	12.0 7.25 4.85 12.0	mA	$V_{CE} = 5 \text{ V}$, $E_e = .50 \text{ mW/cm}^2$ ⁽³⁾
E_{KP}	Knee Point Irradiance		.02		mW/cm^2	$V_{CE} = 5 \text{ V}$ ⁽⁴⁾
I_{CEO}	Collector-Emitter Dark Current			100	nA	$V_{CE} = 10 \text{ V}$, $E_e = 0$
I_{ECO}	Emitter-Reverse Current			100	μA	$V_{EC} = 0.4 \text{ V}$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30			V	$I_C = 100 \mu\text{A}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			0.4	V	$I_C = 250 \mu\text{A}$, $E_e = .50 \text{ mW/cm}^2$ ⁽³⁾

Typical Performance Curves



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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